

Electronics Overview

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Electronics

- System Overview
- Power
- Backplane
- Readout Module (RM)
- Clock and Control Module (CCM)
- Calibration Module

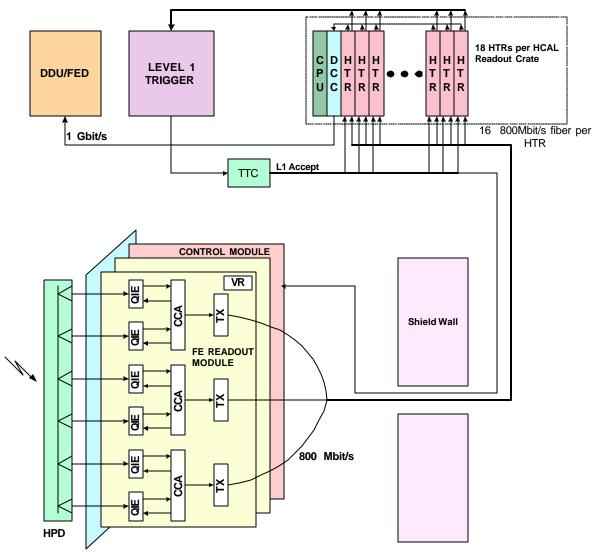
Theresa Shaw (FNAL)



FE/DAQ Readout

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RBX Design Critical for Electonics

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RBX

Provides Power, Cooling, Clock distribution, and **Slow Controls Communication RBX** Design critical for **Connector Choice Backplane development Power/Grounding plans Prototype Work this Summer**



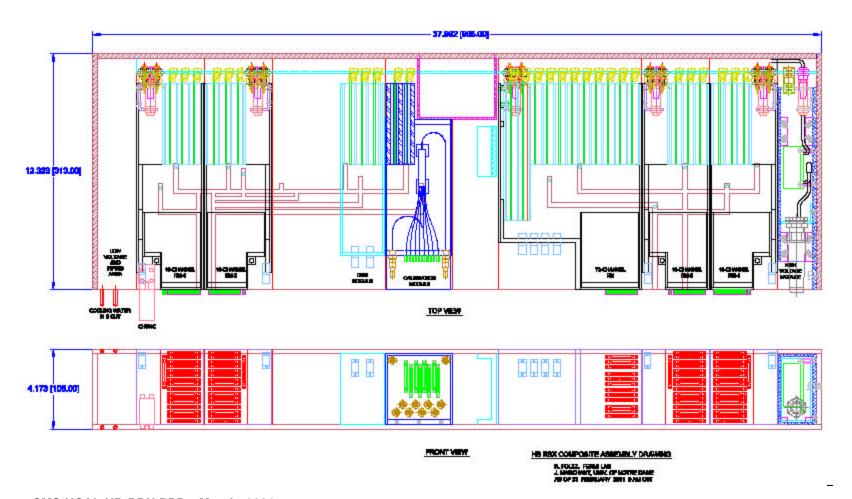
HB RBX

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36 HB RBXs

4968 Channels



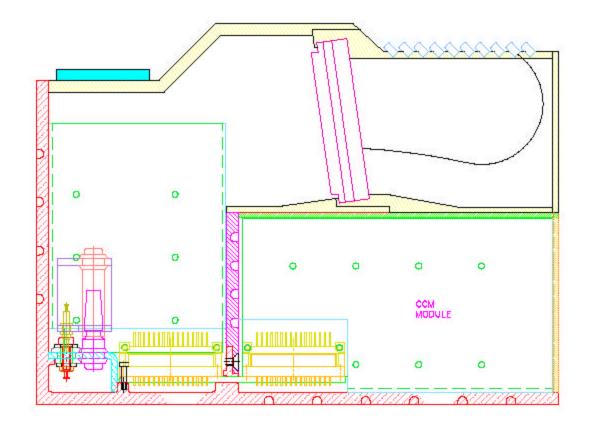


HE Box

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36 HE RBXs

3672 Channels





Power Consumption

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Power Consumption

HB RBX - 298 W 23A@6.5V

33A@4.5V

HE RBX - 205 W 17A@6.5V

21A@4.5V

			CURRENT	and POWER	at BOA	RD LEVEL					
FE Board	QTY/BRD		POWER CONSUPTION					IDLING CURRENT			TOTAL
		VOLTAGE	5	5	2.5	3.3	5	5	2.5	3.3	
Chips											
QIE	6		0.2	0.4							
CCA	3					0.3					
Serializer	3				0.5						
LV regulat	3						0.025	0.025		0.025	
Current / E	Board		0.265	0.505		0.897727					
Total Powe	er / Board										9.044773
Calibratio	n Module			per module)							
		VOLTAGE	5	5	2.5	3.3	5	5	2.5	3.3	
Chips											
QIE	3		0.2	0.4							
CCA	3					0.3					
Serializer	2				0.5						
							2.005	2.005		0.005	
LV regulat	3						0.025	0.025		0.025	
Current / N	Module		0.145	0.265		0.697727					
Total Powe	er / Module										5.804773
ССМ											
		VOLTAGE				3.3					
Chips						5					
LV regulat	tors										
Current / E						1.515152					
Total Power	er / Board										6.818182

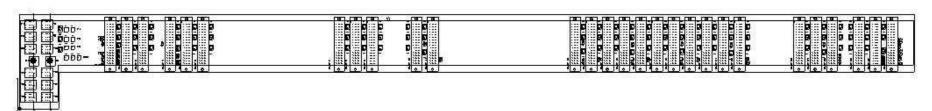


HB Backplane Function

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Backplane

- ~87 CM LONG
- Provides Power
- Distributes 40 MHz Clock (3 load max)
- Provides path for RBXbus (serial communication bus)
- Temperature feedback





Backplane Low Voltage Power Connector

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Product Facts

"Inverse-sex" design meets IEC 950 safety requirements

Current rated at 7.8 amperes per contact, 23.5 amperes per module, fully energized

Sequenced right-angle headers available for "make-first/break-last" applications

ACTION PIN press-fit contacts on both headers and receptacle

Contacts designed for up to 250 mating cycles

Recognized to U.S. and Canadian requirements under the Component **Recognition Program of Underwriters Laboratories Inc.**

Universal Power Module

Low Voltage Distribution

3 Backplane Voltages

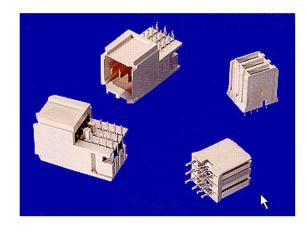
V1 (3 Universal Power Module Connectors for V1)

V2 (2 Universal Power Module Connectors for V2)

V3 (1 Universal Power Module Connectors for V3)

GND (6 Universal Power Module Connectors for GND)

Connectors allow for power sequencing





Backplane Connectors

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Type C and Enhanced Type C Assemblies

Minimum adjacent mounting space required:

12.7 [.500]

Current Rating:

Per DIN 41612*

Voltage Rating:

250 VAC

Dielectric Rating:

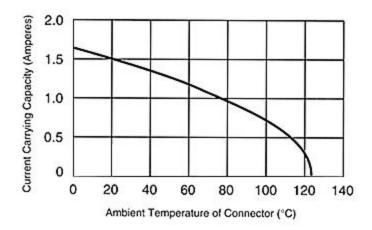
1000 VAC

Contact Resistance:

15 milliohms initial at 100 ma and 50 mv, open circuit



Types B, C, Q and R per DIN 41612





FE Card Pinout

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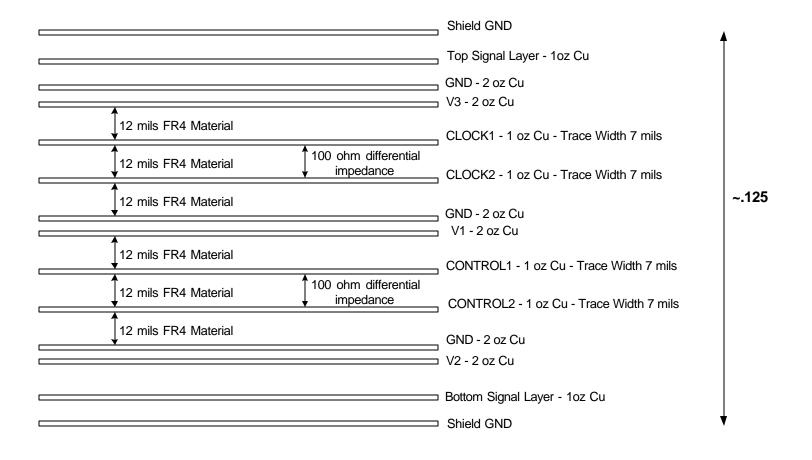
READOUT Card Slot

Pin Number	Row A	Row B	Row C
1	GND	GND	GND
2	V1	V1	V1
3	GND	GND	GND
4	V2	V2	V2
5	GND	GND	GND
6	V3	V3	V3
7	GND	GND	GND
8	MCLK+	D0_CALIB	RESERVED
9	MCLK-	GND	GND
10	GND	GND	TEMP
11	GEO_ADDR(0)	GND	GND
12	GEO_ADDR(1)	GND	RSVD(1)
13	RESET+	GND	RSVD(2)
14	RESET-	GND	SERCLK+
15	BZERO+	GND	SERCLK-
16	BZERO-	GND	SER_DAT



Backplane Stack-up

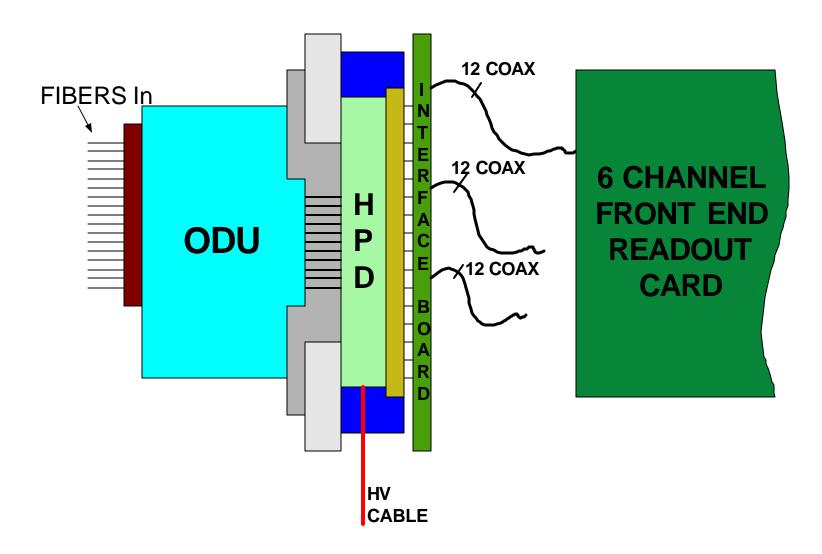
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Readout Module **Overview**

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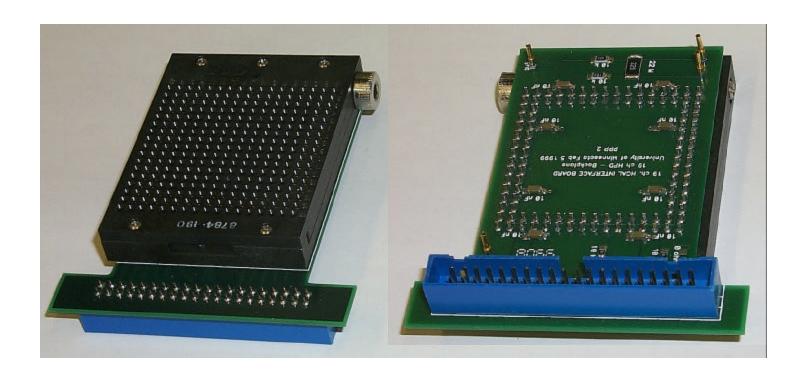




HPD Interface Board

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Signal Cable

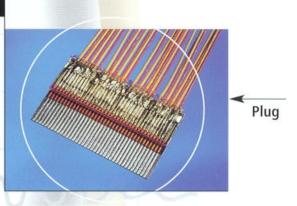
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PICO-FLEX®

OR USE PICO-FLEX:

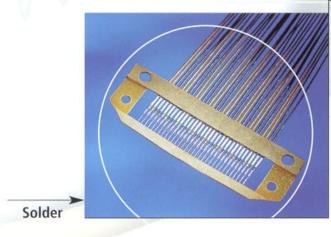
- · Mounted in a ZIF connector surface mounted on a PCB.
- Available in 0,5 mm pitch (0,019").
- Compatible with PICO-COAX® AWG 40 to 46 (50 and 100 pF/m, 15 and 30 pF/ft).
 - · Custom designed versions available on request.



PICO-WELD®

USE PICO-WELD®:

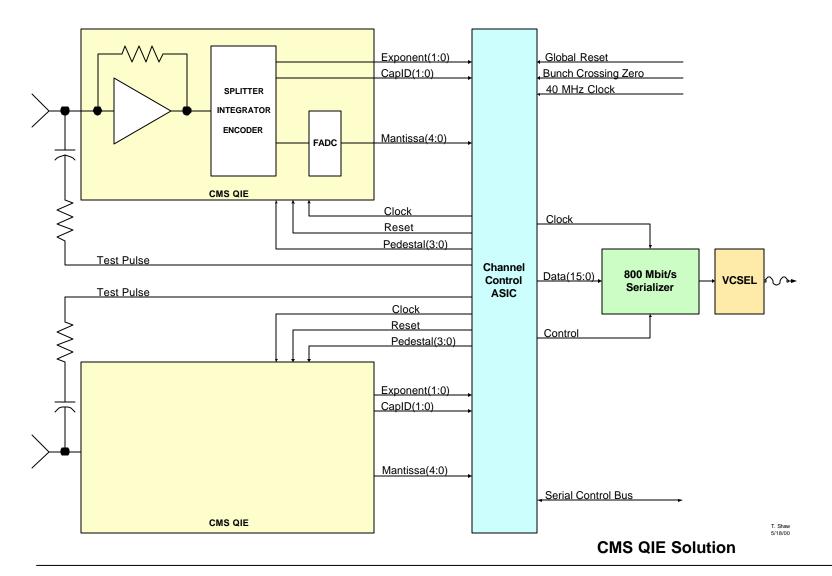
- Solders directly to PC board.
- · Maintains alignment of the PICO-COAX® at a constant pitch.
- · Hot bar system soldering.
- · Available in 32 positions pitch 0,635 mm (0,025").
- Compatible with AWG 40 and 42 (50 and 100 pF/m, 15 and 30 pF/ft).
- · Other constructions available on request





FE Channels

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QIE Description

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QIE

Charge Integrator Encoder

```
4 stage pipelined device (25ns per stage)
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charge collection

settling

readout

reset

Inverting and Non-inverting Inputs

Internal non-linear Flash ADC

Outputs

5 bit mantissa

2 bit range exponent

2 bit Cap ID



QIE Specification

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QIE Design Specifications

Clock Speed >40MHz

Must accept both polarity of charge input

Positive Input gain relative to Negative Input = 2.67

Charge sensitivity Lowest Range = 1fC/LSB

In Calibration Mode 1/3 fC/LSB Range 0 only Linear FADC

Maximum Charge = 9670 fC/25ns

Noise 1.5 LSBs in calibration mode, gaussian

Nominal Pedestal

Calibration Mode nominal Ped = 6.5

Normal Data Mode Ped = .5

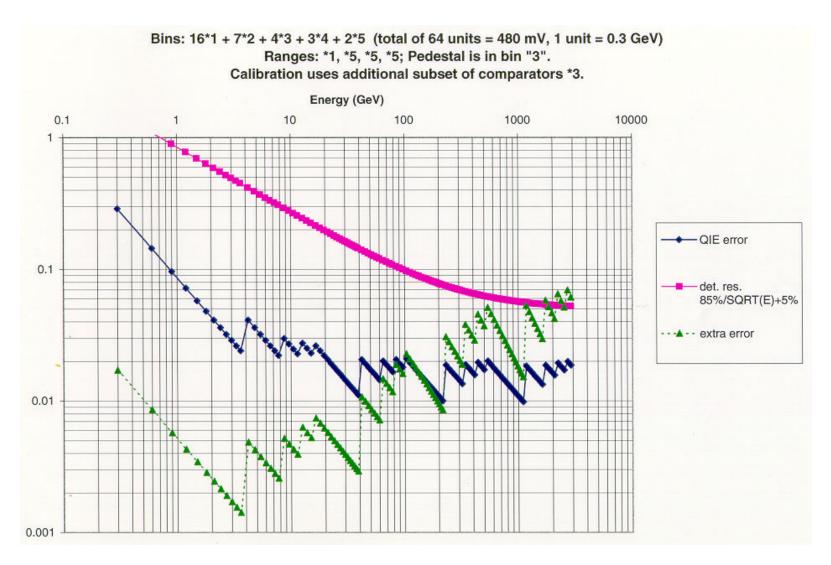
FADC Differential Non-Linearity < .05 LSBs



FLASH ADC Quantization

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Channel Control ASIC

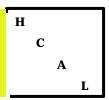
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The CCA provides the following functions:

- The processing and synchronization of data from two QIEs,
- The provision of phase-adjusted QIE clocking signals to run the QIE charge integrator and Flash ADC,
- Checking of the accuracy of the Capacitor IDs, the Cap IDs from different QIEs should be in synchronization,
- The ability to force the QIE to use a given range,
- The ability to set Pedestal DAC values,
- The ability to issue a test pulse trigger,
- The provision of event synchronization checks a crossing counter will be implemented and checked for accuracy with every beam turn marker,
- The ability to send a known pattern to the serial optic link,
- The ability to "reset" the QIE at a known and determined time,
- And, the ability to send and report on any detected errors at a known and determined time.



QIE/CCA **Process Reliability**



AMS 0.8u BiCMOS Process (QIE)

Early Failure rate 0.05 - 0.2%; can be reduced to a few ppm by burn-in

Predicted MTTF (25 sqmm, 55 C) is 1.67E8 hours

Expect less than 1 QIE failure per year

HP/Agilent 0.5u CMOS

Well established Commercial Process



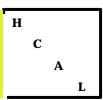
Radiation Tolerance

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- HCAL Radiation Environment
 - Radiation dose over 10yrs 1kRad TID and 4E11 n/cm²
- Electronics
 - QIE and CCA
 - QIE AMS 0.8 μm bi-CMOS process
 - Test bi-polars (TID+bulk damage) and MOS circuits (SEU)
 - CCA HP 0.5 μm bulk-CMOS process
 - Test MOS circuits (SEU)
 - Serializer developed in rad hard process
 - LV regulators developed in rad hard process
 - LEDs, other support components need to test
- Studies performed at Indiana U. Cyclotron (200 MeV protons)
 - Bulk Damage studies
 - Bi-polars dosed to fluence equivalent of 5E11 n/cm²
 - SEU studies
 - AMS and HP test registers

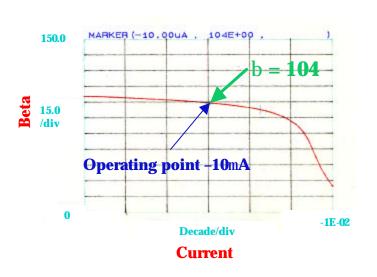


Bi-polar Radiation Studies for QIE

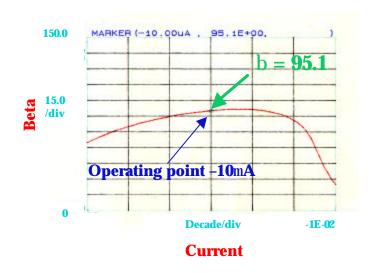


- Bi-polars from AMS 0.8 mm bi-CMOS process
 - Beta for npn-transistors dropped by 5-10% after equivalent of 5E11 n/cm²

Pre-irradiation



Post-irradiation (6 weeks)





SEU Studies for QIE and CCA

- Test registers (min. feature size, min+guard ring, 2Xmin+guard ring, SEU tolerant)
- Xsec results for AMS and HP processes
 - (1-10)E-15 SEU per n/cm² per cell (depending on angle) for conservative design using 2Xmin feature size + guard ring
- For a complex ASIC with 1000 cells and a fluence of 4E11n/cm² over a 10 yr operating period
 - Expect .04-.4 of an upset per ASIC per year



GOL Design Specifications

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Synchronous (constant latency)

Transmission speed

- fast: 1.6 Gbps , 32 bit data input @ 40 MHz
- slow: 0.8 Gbps , 16 bit data input @ 40 MHz

Two encoding schemes

- G-Link
- Fiber channel (8B/10B)

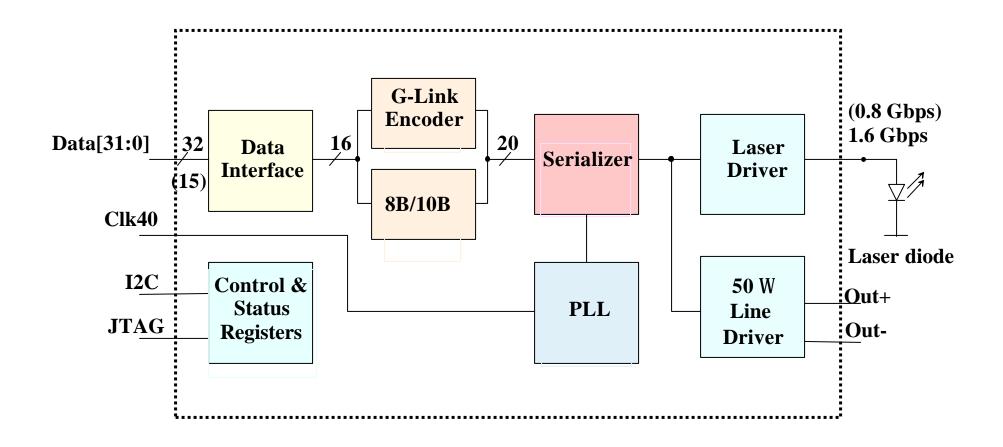
Interfaces for control and status registers

- 12C
- JTAG



Gigabit link (G-Link, 8B/10B optional)

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GOL Radiation hardness

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Deep submicron (0.25 um) CMOS **Enclosed CMOS transistors**

Triple voting in state machines Up-sizing of PLL components Auto-error correction in Config. registers

Single Event Upsets

Can we extrapolate for LHC?

CMS Environment	Pixel R = 4 – 20cm	Endcap ECAL R = 50 - 130cm	Tracker R = 65-120cm	Cavern R = 700 - 1200cm
Error/(chip hour)	1.4 10 ⁻²	1.9 10-4	8.4 10 ⁻⁵	3.1 10 ⁻⁸
#chips for one error each hour!	71	5.3K	12K	32M



VCSEL Selection

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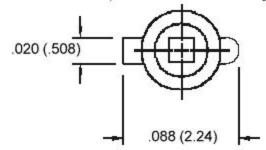
HFE4086-001

VCSEL Components, Data Communications, Flat Window Pillpack, Unattenuate optics, no back monitor photodiode

FEATURES

- Designed for drive currents between 5 mA and 15 mA
- · Optimized for low dependence of electrical properties over temperature
- High speed > 1 Ghz
- Miniature flat-window, pill-pack package

MOUNTING DIMENSIONS (for reference only): in./(mm)



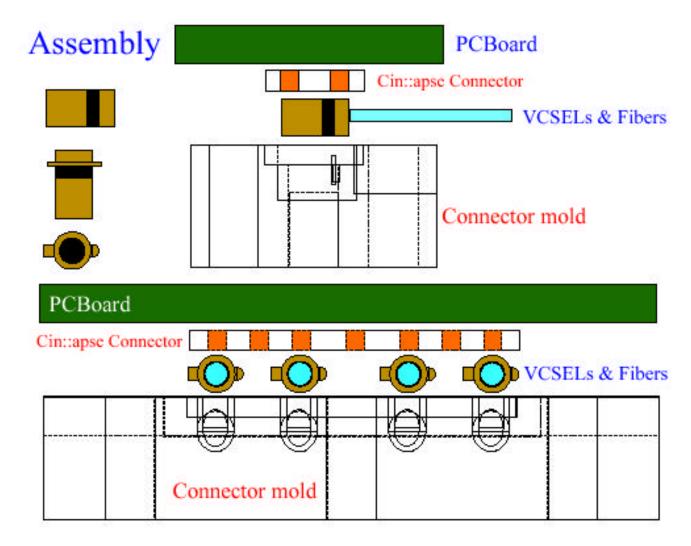




VCSEL Mechanics

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Rad Tolerant Voltage Regulator

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Developed by ST Microelectronics Specified by CERN RD49

Shown to be Rad Hard

Presently fixing overvoltage protection

Prepreduction parts due June 2001

Production parts late 2001

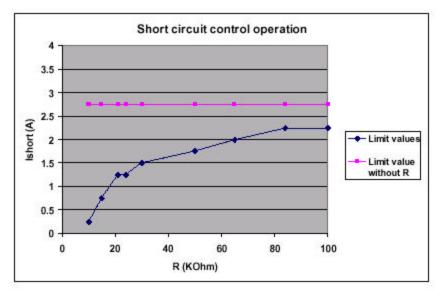
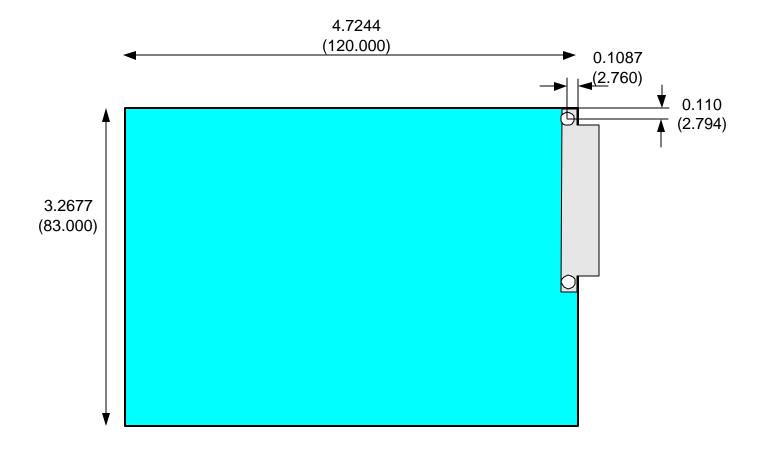


Fig. 7: Tuning of the maximum output current in a 2nd edition prototype regulator (version 2.5 V).



Readout Card Dimension

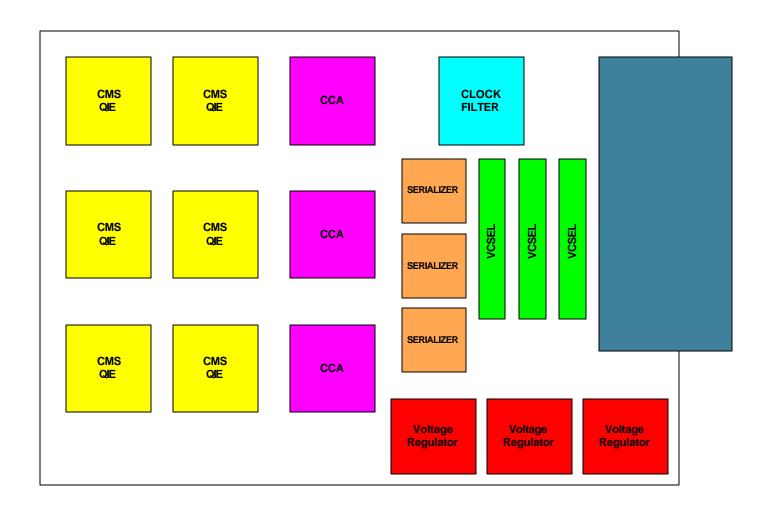
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FE Card Component Area

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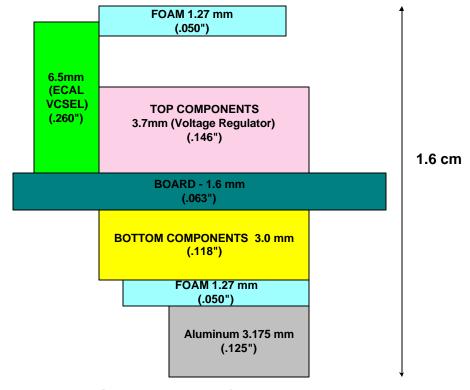




Readout Card **Component Height**



Goal is 1.6 cm stack



Geometric Space For Components



Conclusions

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Need to finalize RBX design

Readout Card connector and mechanics cannot be finalized

Backplane production on hold

Our Goal is to have a working FE/DAQ slice by Summer '01

We would like to have a production RBX to test clock distribution, noise, ...